

BTA10 and BTB10 Series

SNUBBERLESS™ & STANDARD

10A TRIACs

Table 1: Main Features

Symbol	Value	Unit
I _{T(RMS)}	10	А
V _{DRM} /V _{RRM}	600 and 800	V
I _{GT (Q1})	25 to 50	mA

DESCRIPTION

Available either in through-hole or surface-mount packages, the **BTA10** and **BTB10** triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation in light dimmers, motor speed controllers,...

The snubberless version (W suffix) is specially recommended for use on inductive loads, thanks to their high commutation performances.

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at $2500V_{RMS}$) complying with UL standards (File ref.: E81734).

Table 3: Absolute Maximum Ratings

GO	
A1 ⁴ A2 _G	A2 A1 A2 G
TO-220AB Insulated (BTA10)	TO-220AB (BTB10)

 Table 2: Order Codes

Part Number	Marking
BTA10-xxxxxRG	See page table 8 on
BTB10-xxxxxRG	page 6

Symbol	Paramet	Parameter				
I	RMS on-state current (full sine	TO-220AB $T_c = 105^{\circ}C$		10	А	
I _{T(RMS)}	wave)	TO-220AB Ins.	$T_c = 95^{\circ}C$	10	A	
I _{TSM}	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	100	А	
· I SM	current (full cycle, T_j initial = 25°C)	F = 60 Hz	t = 16.7 ms	105	~	
l²t	I ² t Value for fusing	t _p = 10 ms		55	A²s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 125°C	50	A/µs	
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	T _j = 25°C	V _{DSM} /V _{RSM} + 100	V	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125°C	4	А	
P _{G(AV)}	Average gate power dissipation $T_j = 125^{\circ}C$			1	W	
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C	

February 2006

BTA10 and BTB10 Series

Tables 4: Electrical Characteristics (T_j = 25°C, unless otherwise specified)

SNUBBERLESS (3 quadrants)

Symbol Test Conditions		Quadrant		BTA10	BTB10	Unit
Symbol				CW	BW	Onit
I _{GT} (1)	$V_{D} = 12 V R_{I} = 33 \Omega$	- -	MAX.	35	50	mA
V _{GT}		- -	MAX.	1	.3	V
V _{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ}\text{C}$	- -	MIN.	0.2		V
I _H (2)	I _T = 500 mA		MAX.	35	50	mA
lı I	$I_{G} = 1.2 I_{GT}$	-	MAX.	50	70	mA
·L		II	1017 0 4.	60	80	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $T_j = 125^{\circ}C$		MIN.	500	1000	V/µs
(dl/dt)c (2)	Without snubber $T_j = 125^{\circ}C$		MIN.	5.5	9.0	A/ms

Standard (4 quadrants)

Symbol	Test Conditions Quadrant			BTA10	BTB10	Unit
Symbol				С	В	Omi
I _{GT} (1)		- -	MAX.	25	50	mA
	$V_{\rm D} = 12 \text{ V}$ $R_{\rm L} = 33 \Omega$ IV			50	100	
V _{GT}		ALL	MAX.	1	.3	V
V _{GD}	$V_{D} = V_{DRM} R_{L} = 3.3 \text{ k}\Omega T_{j} = 125^{\circ}\text{C} \qquad \text{ALL}$		MIN.	0.2		V
I _H (2)	I _T = 500 mA		MAX.	25	50	mA
I,	I _G = 1.2 I _{GT}	I - III - IV	MAX.	40	50	mA
·L				80	100	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $T_j = 125^{\circ}C$		MIN.	200	400	V/µs
(dV/dt)c (2)	$(dI/dt)c = 4.4 \text{ A/ms}$ $T_j = 125^{\circ}$	C	MIN.	5	10	V/µs

Table 5: Static Characteristics

Symbol	Test Conditions			Value	Unit
V _T (2)	I _{TM} = 14 A t _p = 380 μs	T _j = 25°C	MAX.	1.55	V
V _{t0} (2)	Threshold voltage	T _j = 125°C	MAX.	0.85	V
R _d (2)	Dynamic resistance	T _j = 125°C	MAX.	40	mΩ
I _{DRM}	V _{DRM} = V _{RRM}	$T_j = 25^{\circ}C$	MAX. 5		μA
I _{RRM}	VDRM – VRRM	T _j = 125°C	IVI/AA.	1	mA

57

Note 1: minimum $\rm I_{GT}$ is guaranted at 5% of $\rm I_{GT}$ max.

Note 2: for both polarities of A2 referenced to A1.

Symbol	Parameter		Value	Unit
P	lunction to coop (AC)	TO-220AB	1.5	°C/W
R _{th(j-c)} Junction to case (AC)	TO-220AB Insulated	2.4	0/00	
Б	lunation to ambient	TO-220AB	00	°C/M
R _{th(j-a)}	Junction to ambient	TO-220AB Insulated	60	°C/W

Table 6: Thermal resistance

Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

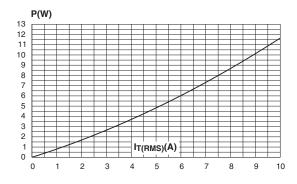
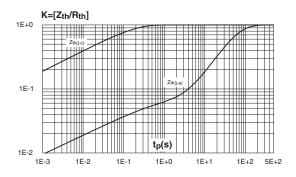


Figure 3: Relative variation of thermal impedance versus pulse duration



57

Figure 2: RMS on-state current versus case temperature (full cycle)

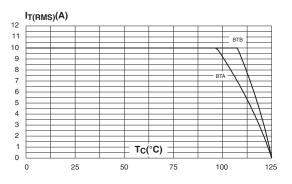


Figure 4: On-state characteristics (maximum values)

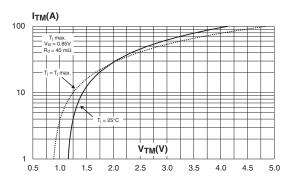


Figure 5: Surge peak on-state current versus number of cycles

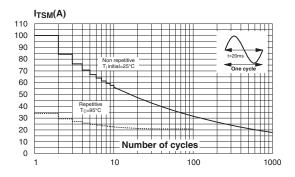


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

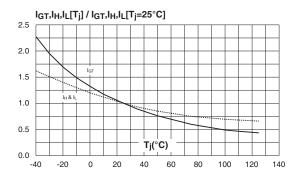
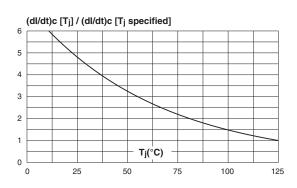


Figure 9: Relative variation of critical rate of decrease of main current versus junction temperature



4/7

Figure 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of l^2t

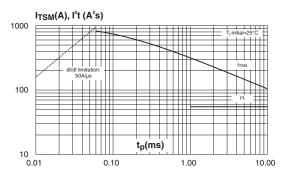
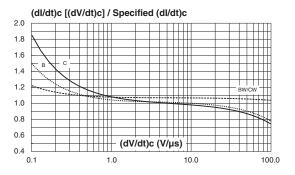
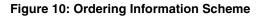


Figure 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)







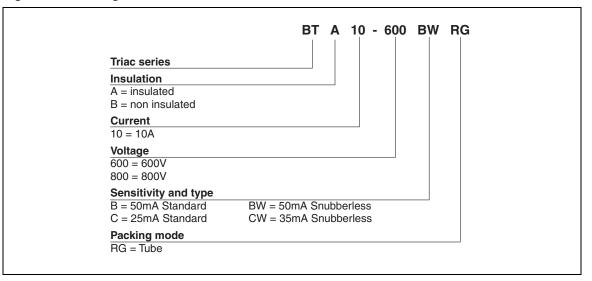


Table 7: Product Selector

Part Number	Voltag	Voltage (xxx)		Туре	
Fait Number	600 V	800 V	 Sensitivity 	туре	Package
BTA/BTB10-xxxB	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB10-xxxBW	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB10-xxxC	Х	Х	25 mA	Standard	TO-220AB
BTA/BTB10-xxxCW	Х	Х	35 mA	Snubberless	TO-220AB

BTB: non insulated TO-220AB package



			İ		DIMEN	SIONS		
		REF.	Mi	illimete	ers		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
в	с	Α	15.20		15.90	0.598		0.625
	b2	a1		3.75			0.147	
		a2	13.00		14.00	0.511		0.551
	F	В	10.00		10.40	0.393		0.409
		b1	0.61		0.88	0.024		0.034
A		b2	1.23		1.32	0.048		0.051
14 13		С	4.40		4.60	0.173		0.181
	c2	c1	0.49		0.70	0.019		0.027
	<u>←→</u>	c2	2.40		2.72	0.094		0.107
12 a2		е	2.40		2.70	0.094		0.106
		F	6.20		6.60	0.244		0.259
	м	ØI	3.75		3.85	0.147		0.151
→ I → I → I → I → I → I → I → I → I →	⊶ c1	14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	

Figure 11: TO-220AB (insulated and non insulated) Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BTA/BTB10-xxxyzRG	BTA/BTB10-xxxyz	TO-220AB	2.3 g	50	Tube

Note: xxx = voltage, yy = sensitivity, z = type

Table 9: Revision History

Date	Revision	Description of Changes
Apr-2002	5A	Last update.
13-Feb-2006	6	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.

/

6/7

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America www.st.com

